

L Number	Hits	Search Text	DB	Time stamp
3	4	insulating adj underlay	USPAT; US-PGPUB	2003/03/19 07:57
4	0	insulative adj underlay	USPAT; US-PGPUB	2003/03/19 07:57
5	0	insulation adj underlay	USPAT; US-PGPUB	2003/03/19 07:57
6	1	dielectric adj underlay	USPAT; US-PGPUB	2003/03/19 09:02
9	0	mosfet and (substrate adj ((mutual adj conductance) or (cut adj off adj frequency) or (flicker adj noise) or (electrostatic adj discharge) or (drain adj withstand adj voltage) or (dielectric adj breakdown) or (leakage adj current)))	USPAT; US-PGPUB	2003/03/19 09:08
10	69	mosfet and (substrate adj ((mutual adj conductance) or (cut adj off adj frequency) or (flicker adj noise) or (electrostatic adj discharge) or (drain adj withstand adj voltage) or (dielectric adj breakdown) or (leakage adj current)))	USPAT; US-PGPUB	2003/03/19 09:14
11	898	mosfet and (substrate with ((mutual adj conductance) or (cut adj off adj frequency) or (flicker adj noise) or (electrostatic adj discharge) or (drain adj withstand adj voltage) or (dielectric adj breakdown) or (leakage adj current)))	USPAT; US-PGPUB	2003/03/19 09:16
12	518	(mosfet and (substrate with ((mutual adj conductance) or (cut adj off adj frequency) or (flicker adj noise) or (electrostatic adj discharge) or (drain adj withstand adj voltage) or (dielectric adj breakdown) or (leakage adj current)))) and 257/\$.ccls.	USPAT; US-PGPUB	2003/03/19 09:51
13	1	defect adj density adj measuring adj method	USPAT; US-PGPUB	2003/03/19 09:52
14	2	defect adj density adj measuring	USPAT; US-PGPUB	2003/03/19 09:53
15	15	measuring adj defect adj density	USPAT; US-PGPUB	2003/03/19 09:55
16	409	(defect adj density) with (soi or sos)	USPAT; US-PGPUB	2003/03/19 09:56
17	0	((defect adj density) with (soi or sos)) and 257./\$.ccls.	USPAT; US-PGPUB	2003/03/19 09:56
18	147	((defect adj density) with (soi or sos)) and 257/\$.ccls.	USPAT; US-PGPUB	2003/03/19 10:11
19	12	((defect adj density) with (soi or sos)) and 257/\$.ccls.) and (surface adj roughness)	USPAT; US-PGPUB	2003/03/19 10:17
20	455	soi and (surface adj roughness)	USPAT; US-PGPUB	2003/03/19 10:25
21	67	soi with (surface adj roughness)	USPAT; US-PGPUB	2003/03/19 10:38
22	2	soi with (surface adj roughness) with (defect adj density)	USPAT; US-PGPUB	2003/03/19 10:39
23	5	soi same (surface adj roughness) same (defect adj density)	USPAT; US-PGPUB	2003/03/19 10:42
24	77	soi and (surface adj roughness) and (defect adj density)	USPAT; US-PGPUB	2003/03/19 13:44
25	309	method adj (fabricating or producing or manufacturing) adj semiconductor adj substrate	USPAT; US-PGPUB	2003/03/19 13:46
26	112	(method adj (fabricating or producing or manufacturing) adj semiconductor adj substrate) and (soi or (silicon adj on adj insulator))	USPAT; US-PGPUB	2003/03/19 13:48
27	10	(method adj (fabricating or producing or manufacturing) adj semiconductor adj substrate) and (first adj ion adj implantation)	USPAT; US-PGPUB	2003/03/19 13:52

28	57	soi and (anneal or heat) and (first adj ion adj implantation)	USPAT; US-PGPUB	2003/03/19 14:32
29	0	soi with (ion adj implanting) with silicon with amorphous with (anneal or heat)	USPAT; US-PGPUB	2003/03/19 14:34
30	0	soi with (ion adj implantation) with silicon with amorphous with (anneal or heat)	USPAT; US-PGPUB	2003/03/19 14:34
31	2	soi same (ion adj implantation) same silicon same amorphous same (anneal or heat)	USPAT; US-PGPUB	2003/03/19 14:37
32	310	(ion adj implantation) same silicon same amorphous same (anneal or heat)	USPAT; US-PGPUB	2003/03/19 14:38
33	208	((ion adj implantation) same silicon same amorphous same (anneal or heat)) and 438/\$.ccls.	USPAT; US-PGPUB	2003/03/19 14:40
-	649	(sos or soi) and (epitaxially adj grown adj (si or silicon))	USPAT; US-PGPUB	2002/12/11 08:14
-	354	(sos or soi) and (epitaxially adj grown adj (si or silicon)) and (single adj (crystal or crystalline))	USPAT; US-PGPUB	2002/12/11 08:15
-	100	(sos or soi) and (epitaxially adj grown adj (si or silicon)) and (single adj (crystal or crystalline)) and (method adj (manufacturing or producing))	USPAT; US-PGPUB	2002/12/11 08:42
-	9	(sos or soi) and (epitaxially adj grown adj (si or silicon)) and (single adj (crystal or crystalline)) and (method adj (manufacturing or producing)) and (defect adj density)	USPAT; US-PGPUB	2002/12/11 09:24
-	0	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (pits adj per adj unit)	USPAT; US-PGPUB	2002/12/11 09:24
-	1	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (crystalline adj oxide)	USPAT; US-PGPUB	2002/12/11 09:25
-	0	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (iodine adj etch)	USPAT; US-PGPUB	2002/12/11 09:26
-	118	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (crystalline adj silicon)	USPAT; US-PGPUB	2002/12/12 07:53
-	14	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (fluoride adj layer)	USPAT; US-PGPUB	2002/12/11 09:30
-	46	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (defect adj density)	USPAT; US-PGPUB	2002/12/11 11:10
-	76	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (surface adj roughness)	USPAT; US-PGPUB	2002/12/11 11:10
-	0	5439843.pn. and sio	USPAT; US-PGPUB	2002/12/12 09:38
-	0	5439843.pn. and sio2	USPAT; US-PGPUB	2002/12/12 07:54
-	1	5439843.pn. and (defect adj density)	USPAT; US-PGPUB	2002/12/12 08:05
-	1	5439843.pn. and oxide	USPAT; US-PGPUB	2002/12/12 07:56
-	1	5439843.pn. and heat	USPAT; US-PGPUB	2002/12/12 07:56
-	0	5439843.pn. and pits	USPAT; US-PGPUB	2002/12/12 08:07
-	0	5439843.pn. and (surface adj roughness)	USPAT; US-PGPUB	2002/12/12 08:09
-	1	5439843.pn. and nm	USPAT; US-PGPUB	2002/12/12 08:08
-	0	5439843.pn. and roughness	USPAT; US-PGPUB	2002/12/12 08:09
-	0	5439843.pn. and rough	USPAT; US-PGPUB	2002/12/12 08:09

-	1	5439843.pn. and surface	USPAT; US-PGPUB	2002/12/12 08:09
-	0	5439843.pn. and iodine	USPAT; US-PGPUB	2002/12/12 08:41
-	0	5869387.pn. and iodine	USPAT; US-PGPUB	2002/12/12 09:39
-	216	silicon adj soi	USPAT; US-PGPUB	2002/12/12 09:09
-	2	(silicon adj soi) and (method adj (producing or making or manufacturing) adj semiconductor adj substrate)	USPAT; US-PGPUB	2002/12/12 09:00
-	215	(soi or sos) and (method adj (producing or making or manufacturing) adj semiconductor adj substrate)	USPAT; US-PGPUB	2002/12/12 09:00
-	0	epitaxially adj growing adj silicon adj silicon	USPAT; US-PGPUB	2002/12/12 09:10
-	0	epitaxially adj growing adj silicon adj layer adj silicon	USPAT; US-PGPUB	2002/12/12 09:10
-	0	epitaxial adj silicon adj layer adj silicon	USPAT; US-PGPUB	2002/12/12 09:10
-	164	(epitaxially adj growing adj silicon) same silicon	USPAT; US-PGPUB	2002/12/12 09:40
-	0	5439843.pn. and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:39
-	0	5869387.pn. and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:40
-	0	5629217.pn. and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:40
-	0	5066610.pn. and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:40
-	10	((epitaxially adj growing adj silicon) same silicon) and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:42
-	0	(low adj defect adj density adj silicon adj layer) and (soi or sos)	USPAT; US-PGPUB	2002/12/12 09:43
-	0	(low adj defect adj density adj silicon adj layer)	USPAT; US-PGPUB	2002/12/12 09:43
-	10	(low adj defect adj density adj layer)	USPAT; US-PGPUB	2002/12/12 09:45
-	705	(low adj defect adj density) and (soi or sos)	USPAT; US-PGPUB	2002/12/12 09:47
-	153	((low adj defect adj density) with silicon)and (soi or sos)	USPAT; US-PGPUB	2002/12/12 09:47
-	153	((low adj defect adj density) with silicon) and (soi or sos)	USPAT; US-PGPUB	2002/12/12 14:17
-	5	(first adj ion adj implantation) and (soi or sos) and (epitaxially adj grown adj silicon)	USPAT; US-PGPUB	2002/12/12 14:24
-	0	(first adj ion adj implantation) and ((silicon adj insulator) or (silicon adj sapphire)) and (epitaxially adj grown adj silicon)	USPAT; US-PGPUB	2002/12/12 14:24
-	5	(first adj ion adj implantation) and (epitaxially adj grown adj silicon)	USPAT; US-PGPUB	2002/12/12 14:24
-	37	(first adj ion adj implantation) and ((silicon adj insulator) or (silicon adj sapphire))	USPAT; US-PGPUB	2002/12/12 14:25
-	1628	simox	USPAT; US-PGPUB	2002/12/13 20:10

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70	1628	simox	USPAT; US-PGPUB	2002/12/13 20:10
-	649	((sos or soi) and (epitaxially adj grown adj (si or silicon)))	USPAT; US-PGPUB	2002/12/11 08:14
-	354	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (single adj (crystal or crystalline))	USPAT; US-PGPUB	2002/12/11 08:15
-	100	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (single adj (crystal or crystalline)) and (method adj (manufacturing or producing))	USPAT; US-PGPUB	2002/12/11 08:42
-	9	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (single adj (crystal or crystalline)) and (method adj (manufacturing or producing)) and (defect adj density)	USPAT; US-PGPUB	2002/12/11 09:24
-	0	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (pits adj per adj unit)	USPAT; US-PGPUB	2002/12/11 09:24
-	1	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (crystalline adj oxide)	USPAT; US-PGPUB	2002/12/11 09:25
-	0	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (iodine adj etch)	USPAT; US-PGPUB	2002/12/11 09:26
-	118	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (crystalline adj silicon)	USPAT; US-PGPUB	2002/12/12 07:53
-	14	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (fluoride adj layer)	USPAT; US-PGPUB	2002/12/11 09:30
-	46	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (defect adj density)	USPAT; US-PGPUB	2002/12/11 11:10
-	76	((sos or soi) and (epitaxially adj grown adj (si or silicon))) and (surface adj roughness)	USPAT; US-PGPUB	2002/12/11 11:10
-	0	5439843.pn. and sio	USPAT; US-PGPUB	2002/12/12 09:38
-	0	5439843.pn. and sio2	USPAT; US-PGPUB	2002/12/12 07:54
-	1	5439843.pn. and (defect adj density)	USPAT; US-PGPUB	2002/12/12 08:05
-	1	5439843.pn. and oxide	USPAT; US-PGPUB	2002/12/12 07:56
-	1	5439843.pn. and heat	USPAT; US-PGPUB	2002/12/12 07:56
-	0	5439843.pn. and pits	USPAT; US-PGPUB	2002/12/12 08:07
-	0	5439843.pn. and (surface adj roughness)	USPAT; US-PGPUB	2002/12/12 08:09
-	1	5439843.pn. and nm	USPAT; US-PGPUB	2002/12/12 08:08
-	0	5439843.pn. and roughness	USPAT; US-PGPUB	2002/12/12 08:09
-	0	5439843.pn. and rough	USPAT; US-PGPUB	2002/12/12 08:09
-	1	5439843.pn. and surface	USPAT; US-PGPUB	2002/12/12 08:09
-	0	5439843.pn. and iodine	USPAT; US-PGPUB	2002/12/12 08:41
-	0	5869387.pn. and iodine	USPAT; US-PGPUB	2002/12/12 09:39
-	216	silicon adj soi	USPAT; US-PGPUB	2002/12/12 09:09
-	2	((silicon adj soi) and (method adj (producing or making or manufacturing) adj semiconductor adj substrate))	USPAT; US-PGPUB	2002/12/12 09:00

-	215	(soi or sos) and (method adj (producing or making or manufacturing) adj semiconductor adj substrate)	USPAT; US-PGPUB	2002/12/12 09:00
-	0	epitaxially adj growing adj silicon adj silicon	USPAT; US-PGPUB	2002/12/12 09:10
-	0	epitaxially adj growing adj silicon adj layer adj silicon	USPAT; US-PGPUB	2002/12/12 09:10
-	0	epitaxial adj silicon adj layer adj silicon	USPAT; US-PGPUB	2002/12/12 09:10
-	164	(epitaxially adj growing adj silicon) same silicon	USPAT; US-PGPUB	2002/12/12 09:40
-	0	5439843.pn. and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:39
-	0	5869387.pn. and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:40
-	0	5629217.pn. and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:40
-	0	5066610.pn. and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:40
-	10	((epitaxially adj growing adj silicon) same silicon) and (low adj defect adj density)	USPAT; US-PGPUB	2002/12/12 09:42
-	0	(low adj defect adj density adj silicon adj layer) and (soi or sos)	USPAT; US-PGPUB	2002/12/12 09:43
-	0	(low adj defect adj density adj silicon adj layer)	USPAT; US-PGPUB	2002/12/12 09:43
-	10	(low adj defect adj density adj layer)	USPAT; US-PGPUB	2002/12/12 09:45
-	705	(low adj defect adj density) and (soi or sos)	USPAT; US-PGPUB	2002/12/12 09:47
-	153	((low adj defect adj density) with silicon)and (soi or sos)	USPAT; US-PGPUB	2002/12/12 09:47
-	153	((low adj defect adj density) with silicon) and (soi or sos)	USPAT; US-PGPUB	2002/12/12 14:17
-	5	(first adj ion adj implantation) and (soi or sos) and (epitaxially adj grown adj silicon)	USPAT; US-PGPUB	2002/12/12 14:24
-	0	(first adj ion adj implantation) and ((silicon adj insulator) or (silicon adj sapphire)) and (epitaxially adj grown adj silicon)	USPAT; US-PGPUB	2002/12/12 14:24
-	5	(first adj ion adj implantation) and (epitaxially adj grown adj silicon)	USPAT; US-PGPUB	2002/12/12 14:24
-	37	(first adj ion adj implantation) and ((silicon adj insulator) or (silicon adj sapphire))	USPAT; US-PGPUB	2002/12/12 14:25